

Silicon NPN Power Transistors

2SD1492

DESCRIPTION

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- With TO-3PN package
- High voltage ,high reliability
- Wide area of safe operation

APPLICATIONS

- High voltage power switching TV horizontal deflection output applications

PINNING

| PIN | DESCRIPTION                          |
|-----|--------------------------------------|
| 1   | Base                                 |
| 2   | Collector;connected to mounting base |
| 3   | Emitter                              |

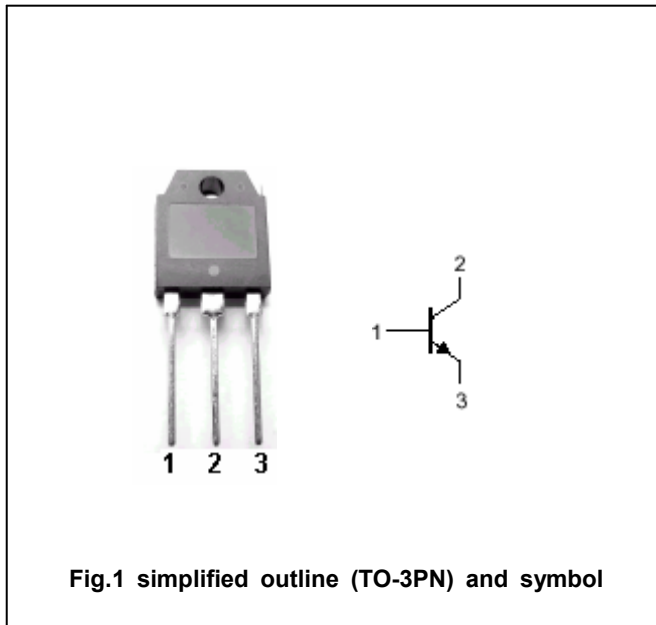


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

| SYMBOL           | PARAMETER                   | CONDITIONS           | VALUE   | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V <sub>CBO</sub> | Collector-base voltage      | Open emitter         | 1500    | V    |
| V <sub>CEO</sub> | Collector-emitter voltage   | Open base            | 600     | V    |
| V <sub>EBO</sub> | Emitter-base voltage        | Open collector       | 6       | V    |
| I <sub>C</sub>   | Collector current           |                      | 1.5     | A    |
| P <sub>C</sub>   | Collector power dissipation | T <sub>C</sub> =25°C | 50      | W    |
| T <sub>j</sub>   | Junction temperature        |                      | 150     | °C   |
| T <sub>stg</sub> | Storage temperature         |                      | -45~150 | °C   |

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

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| SYMBOL               | PARAMETER                            | CONDITIONS                                    | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|-----|------|
| V <sub>(BR)EBO</sub> | Emitter-base breakdown voltage       | I <sub>E</sub> =10mA; I <sub>C</sub> =0       | 6   |      |     | V    |
| V <sub>(BR)CEO</sub> | Collector-emitter breakdown voltage  | I <sub>C</sub> =10mA; R <sub>BE</sub> =∞      | 600 |      |     | V    |
| V <sub>CEsat</sub>   | Collector-emitter saturation voltage | I <sub>C</sub> =1.2A; I <sub>B</sub> =0.3A    |     |      | 5.0 | V    |
| V <sub>BEsat</sub>   | Base-emitter saturation voltage      | I <sub>C</sub> =1.2A; I <sub>B</sub> =0.3A    |     |      | 1.5 | V    |
| I <sub>CEx</sub>     | Collector cut-off current            | V <sub>CE</sub> =1500V; V <sub>BE</sub> =1.5V |     |      | 1.0 | mA   |
| I <sub>EBO</sub>     | Emitter cut-off current              | V <sub>EB</sub> =6V; I <sub>C</sub> =0        |     |      | 1.0 | mA   |
| h <sub>FE</sub>      | DC current gain                      | I <sub>C</sub> =0.3A ; V <sub>CE</sub> =5V    | 10  |      | 30  |      |

PACKAGE OUTLINE

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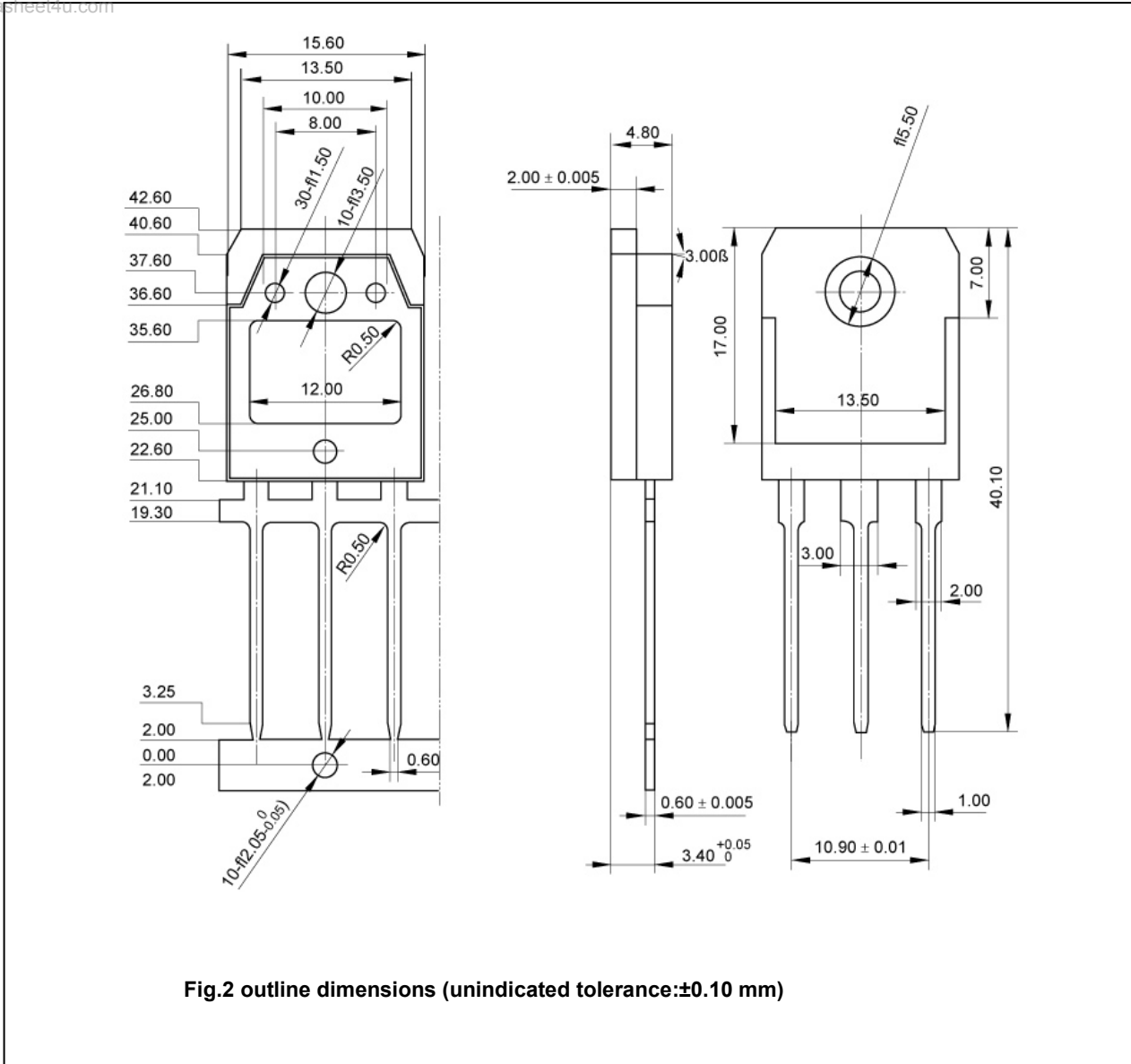


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)